L Number	Hits	Search Text	DB	Time stamp
1	79113	LSI	USPAT;	2004/09/16 09:51
	•		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	22650	LSI and (integrated adj circuit)	USPAT;	2004/09/16 09:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
3	22650	"LSI" and (integrated adj circuit)	USPAT;	2004/09/16 09:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
4	2373	"LSI" and (integrated adj circuit) and expansion	USPAT;	2004/09/16 09:52
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1	•	IBM_TDB	
5	951	"LSI" and (integrated adj circuit) and (thermal adj expansion)	USPAT;	2004/09/16 09:53
		Bor and (integrated adj entrate) and (internal adj entrate)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	115	("LSI" adj circuit) and (thermal adj expansion)	USPAT;	2004/09/16 09:55
0	113	(LS1 adj circuit) and (incrinar adj expansion)	US-PGPUB;	200 17 037 10 03.33
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
7	96	("LSI" adj circuit) and (thermal adj expansion) and substrate	USPAT;	2004/09/16 09:59
1 '	1 30	(LSI adj circuit) and (incrinal adj expansion) and saostrate	US-PGPUB;	200 11 031 10 03133
			EPO; JPO;	
			DERWENT;	
ŀ			IBM_TDB	
8	22	("LSI" adj circuit) and substrate and ((aluminum adj oxide) or (platinum	USPAT;	2004/09/16 10:08
٥		NEAR doped))	US-PGPUB;	2004/05/10 10:00
		NEAR doped))	EPO; JPO;	
ŀ			DERWENT;	
			IBM_TDB	
9	_	("LSI" adj circuit) and (substrate NEAR2 ((aluminum adj oxide) or	USPAT;	2004/09/16 10:08
9	0	(platinum NEAR doped)))	US-PGPUB;	2004/03/10 10:00
		(plainum NEAR doped)))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
10	22	("LSI" adj circuit) and substrate and ((aluminum adj oxide) or (platinum	USPAT;	2004/09/16 10:12
10	22	NEAR doped))	US-PGPUB;	2004/05/10 10:12
	İ	NEAR doped))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
11	0	("LSI" adj circuit) and (substrate NEAR ((aluminum adj oxide) or	USPAT;	2004/09/16 10:12
11	U		US-PGPUB;	200-707/10 10.12
		(platinum)))	EPO; JPO;	
			DERWENT;	
		(BECHI J.	IBM_TDB	2004/00/16 10:16
12	4	(USPAT;	2004/09/16 10:16
		("SiO.sub.2")) or (platinum)))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1	i		IBM_TDB	

13	231	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum)))	USPAT; US-PGPUB; EPO; JPO; DERWENT;	72004/09/16 10:16
14	196	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum))) and (metal or plastic)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/16 10:17
15	19	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum))) and (metal and plastic)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/16 10:17
16	1	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) and (platinum))) and (metal and plastic)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/16 10:17
17	1	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) and (platinum))) and (metal or plastic)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/16 10:18
18	196	("LSI") and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum))) and (metal or plastic)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/16 10:20
19	657	(integrated adj circuit) and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum))) and (metal or plastic)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/16 10:20
20	5	(integrated adj circuit) and (substrate NEAR (((aluminum adj oxide) or ("SiO.sub.2")) or (platinum))) and ((metal or plastic) NEAR circuit\$3)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/16 10:25
21	703	(integrated adj circuit) and (substrate NEAR ((aluminum adj oxide) or ("SiO.sub.2"))) or ((platinum adj doped) adj (silicon adj wafer))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/16 10:26
22	0	(integrated adj circuit) and (substrate NEAR ((aluminum adj oxide) or ("SiO.sub.2"))) and ((platinum adj doped) adj (silicon adj wafer))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/16 10:26
23	702	(integrated adj circuit) and (substrate NEAR ((aluminum adj oxide) or ("SiO.sub.2"))) or ((platinum adj doped) adj (silicon adj wafer)) and ("LSI")	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/16 10:26
24	702	(integrated adj circuit) and (substrate NEAR ((aluminum adj oxide) or ("SiO.sub.2"))) or ((platinum adj doped) adj (silicon adj wafer)) and ("LSI") and metal	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/16 10:27

25	89	(integrated adj circuit) and (substrate NEAR ((aluminum adj oxide) or	USPAT;	2004/09/16 10:27
		("SiO.sub.2"))) and ("LSI") and metal	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/00/14 10 22
26	0	(integrated adj circuit) and ((platinum adj doped) adj (silicon adj wafer))	USPAT;	2004/09/16 10:27
		and ("LSI") and metal	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		(4.1.2. P. 1. 15. 17.2.12. P. C.S. 1.017.0705. 1	IBM_TDB	2004/00/16 10:27
27	0	((platinum adj doped) adj (silicon adj wafer)) and ("LSI") and metal	USPAT;	2004/09/16 10:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		((1 d)	IBM_TDB USPAT;	2004/09/16 10:27
28	1	((platinum adj doped) adj (silicon adj wafer))	US-PGPUB;	2004/03/10 10.27
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
20	13	((platinum) adj (silicon adj wafer))	USPAT;	2004/09/16 10:28
29	13	((piatilium) auj (sincon auj water))	US-PGPUB;	2004/05/10 10:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
30	2	((platinum) adj (silicon adj wafer)) and (integrated adj circuit)	USPAT;	2004/09/16 10:36
30		((platifically) and (integrated as) victory)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
31	1220	"LSI" and (integrated adj circuit) and metal and plastic	USPAT;	2004/09/16 10:36
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
32	960	"LSI" and (integrated adj circuit) and metal and plastic and substrate	USPAT;	2004/09/16 10:37
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
33	3	"LSI" and (integrated adj circuit) and metal and plastic and (substrate	USPAT;	2004/09/16 10:37
	1	NEAR ((aluminum adj oxide) or platinum))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	1